

Radiation Hardened, High Performance Industry Standard Single-Ended Current Mode PWM Controller

ISL78840ASRH, ISL78841ASRH, ISL78843ASRH, ISL78845ASRH

The ISL7884xASRH is a high performance, radiation hardened drop-in replacement for the popular 28C4x and 18C4x PWM controllers suitable for a wide range of power conversion applications including boost, flyback, and isolated output configurations. Its fast signal propagation and output switching characteristics make this an ideal product for existing and new designs.

Features include up to 13.2V operation, low operating current, 90µA typ start-up current, adjustable operating frequency to 1MHz, and high peak current drive capability with 50ns rise and fall times.

| PART NUMBER | RISING UVLO | MAX. DUTY CYCLE |
|--------------|-------------|-----------------|
| ISL78840ASRH | 7.0 | 100% |
| ISL78841ASRH | 7.0 | 50% |
| ISL78843ASRH | 8.4V | 100% |
| ISL78845ASRH | 8.4V | 50% |

Specifications for Rad Hard QML devices are controlled by the Defense Supply Center in Columbus (DSCC). The SMD numbers listed in the ordering information must be used when ordering.

Detailed Electrical Specifications for the ISL788xASRH are contained in SMD 5962-07249. A "hot-link" is provided on our website for downloading.

Features

- Electrically Screened to DSCC SMD # 5962-07249
- QML Qualified Per MIL-PRF-38535 Requirements
- 1A MOSFET Gate Driver
- 90µA Typ Start-up Current, 125µA Max
- 35ns Propagation Delay Current Sense to Output
- · Fast Transient Response with Peak Current Mode Control
- 9V to 13.2V Operation
- · Adjustable Switching Frequency to 1MHz
- 50ns Rise and Fall Times with 1nF Output Load
- · Trimmed Timing Capacitor Discharge Current for Accurate Deadtime/Maximum Duty Cycle Control
- 1.5MHz Bandwidth Error Amplifier
- · Tight Tolerance Voltage Reference Over Line, Load and Temperature
- ±3% Current Limit Threshold
- · Pb-Free Available (RoHS Compliant)

Applications

- Current Mode Switching Power Supplies
- · Isolated Buck and Flyback Regulators
- Boost Regulators
- · Direction and Speed Control in Motors
- Control of High Current FET Drivers

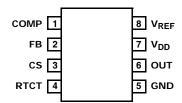
Pin Configurations

ISL78840ASRH, ISL78841ASRH, ISL78843ASRH, ISL78845ASRH (8 LD FLATPACK) TOP VIEW

1 • 8 COMP I VRFF 2 7 J V_{DD} 3 CS T 6 OUT RTCT E GND

1

ISL78840ASRH, ISL78841ASRH, ISL78843ASRH, ISL78845ASRH (8 LD SBDIP) TOP VIEW



Ordering Information

| ORDERING NUMBER | PART NUMBER | TEMP. RANGE (°C) | PACKAGE (Pb-Free) | PKG. DWG. # |
|-----------------------|----------------------------------|---------------------|----------------------|-------------|
| ISL78840ASRHVX/SAMPLE | ISL78840ASRHVX/SAMPLE | -55 to +125 | Die | |
| ISL78840ASRHF/PROTO | ISL78840ASRHF/PROTO (Notes 1, 2) | -55 to +125 | 8 Ld Flatpack | K8.A |
| 5962R0724901QXC | ISL78840ASRHQF (Notes 1, 2) | -55 to +125 | 8 Ld Flatpack | K8.A |
| 5962R0724901VXC | ISL78840ASRHVF (Notes 1, 2) | -55 to +125 | 8 Ld Flatpack | K8.A |
| ISL78840ASRHD/PROTO | ISL78840ASRHD/PROTO (Notes 1, 2) | -55 to +125 | 8 Ld SBDIP | D8.3 |
| 5962R0724901QPC | ISL78840ASRHQD (Notes 1, 2) | -55 to +125 | 8 Ld SBDIP | D8.3 |
| 5962R0724901VPC | ISL78840ASRHVD (Notes 1, 2) | -55 to +125 | 8 Ld SBDIP | D8.3 |
| ISL78841ASRHVX/SAMPLE | ISL78841ASRHVX/SAMPLE | -55 to +125 | Die | |
| ISL78841ASRHF/PROTO | ISL78841ASRHF/PROTO (Notes 1, 2) | -55 to +125 | 8 Ld Flatpack | K8.A |
| 5962R0724902QXC | ISL78841ASRHQF (Notes 1, 2) | -55 to +125 | 8 Ld Flatpack | K8.A |
| 5962R0724902VXC | ISL78841ASRHVF (Notes 1, 2) | -55 to +125 | 8 Ld Flatpack | K8.A |
| ISL78841ASRHD/PROTO | ISL78841ASRHD/PROTO (Notes 1, 2) | -55 to +125 | 8 Ld SBDIP | D8.3 |
| 5962R0724902QPC | ISL78841ASRHQD (Notes 1, 2) | -55 to +125 | 8 Ld SBDIP | D8.3 |
| 5962R0724902VPC | ISL78841ASRHVD (Notes 1, 2) | -55 to +125 | 8 Ld SBDIP | D8.3 |
| ISL78843ASRHVX/SAMPLE | ISL78843ASRHVX/SAMPLE | -55 to +125 | Die | |
| ISL78843ASRHF/PROTO | ISL78843ASRHF/PROTO (Notes 1, 2) | -55 to +125 | 8 Ld Flatpack | K8.A |
| 5962R0724903QXC | ISL78843ASRHQF (Notes 1, 2) | -55 to +125 | 8 Ld Flatpack | K8.A |
| 5962R0724903VXC | ISL78843ASRHVF (Notes 1, 2) | -55 to +125 | 8 Ld Flatpack | K8.A |
| ISL78843ASRHD/PROTO | ISL78843ASRHD/PROTO (Notes 1, 2) | -55 to +125 | 8 Ld SBDIP | D8.3 |
| 5962R0724903QPC | ISL78843ASRHQD (Notes 1, 2) | -55 to +125 | 8 Ld SBDIP | D8.3 |
| 5962R0724903VPC | ISL78843ASRHVD (Notes 1, 2) | -55 to +125 | 8 Ld SBDIP | D8.3 |
| ISL78845ASRHVX/SAMPLE | ISL78845ASRHVX/SAMPLE | -55 to +125 | Die | |
| ISL78845ASRHF/PROTO | ISL78845ASRHF/PROTO (Notes 1, 2) | -55 to +125 | 8 Ld Flatpack | K8.A |
| 5962R0724904QXC | ISL78845ASRHQF (Notes 1, 2) | -55 to +125 | 8 Ld Flatpack | K8.A |
| 5962R0724904VXC | ISL78845ASRHVF (Notes 1, 2) | -55 to +125 | 8 Ld Flatpack | K8.A |
| ISL78845ASRHD/PROTO | ISL78845ASRHD/PROTO (Notes 1, 2) | -55 to +125 | 8 Ld SBDIP | D8.3 |
| 5962R0724904QPC | ISL78845ASRHQD (Notes 1, 2) | -55 to +125 | 8 Ld SBDIP | D8.3 |
| 5962R0724904VPC | ISL78845ASRHVD (Notes 1, 2) | -55 to +125 | 8 Ld SBDIP | D8.3 |

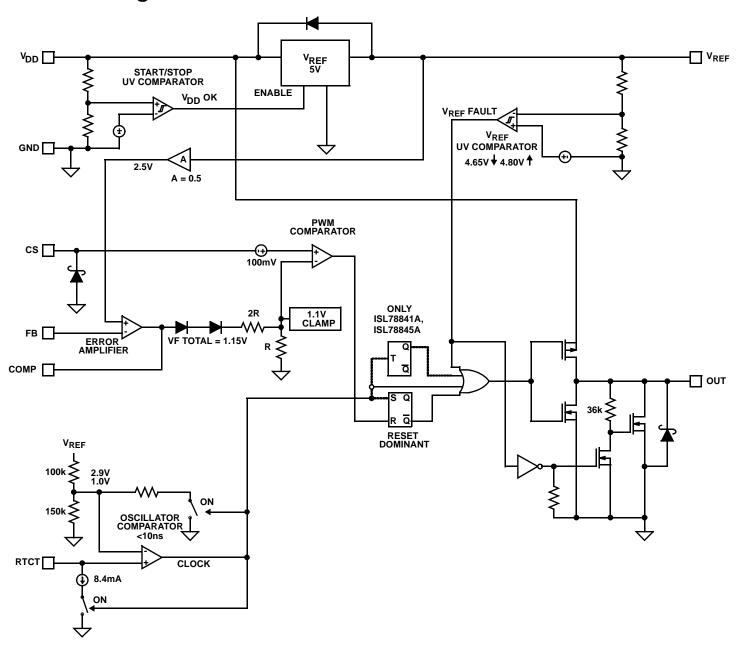
NOTES:

^{1.} These Intersil Pb-free Hermetic packaged products employ 100% Au plate - e4 termination finish, which is RoHS compliant and compatible with both SnPb and Pb-free soldering operations.

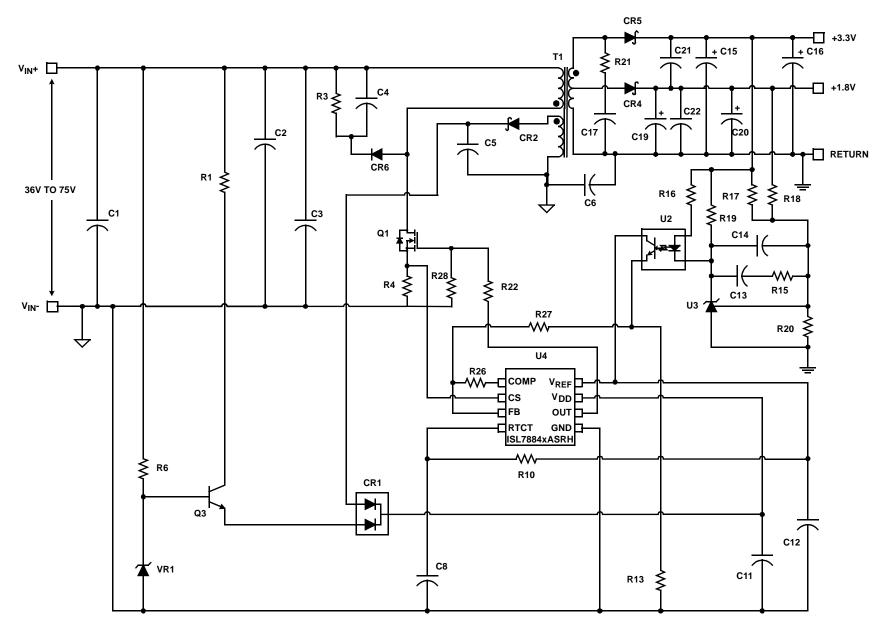
^{2.} For Moisture Sensitivity Level (MSL), please see device information page for ISL78841ASRH, ISL78843ASRH, ISL7884

August 19,

Functional Block Diagram



Typical Application - 48V Input Dual Output Flyback



+VOUT

RETURN

C8

VIN+

 \leq R6

_I C10

Electrical Specifications

Recommended operating conditions unless otherwise noted. Refer to Block Diagram and Typical Application schematic on page 3 and page 4. $V_{DD}=13.2V,\ R_T=10k\Omega,\ C_T=3.3nF,\ T_A=-55\ to\ +125^{\circ}C.$ Typical values are at $T_A=+25^{\circ}C.$

| PARAMETER | TEST CONDITIONS | MIN | TYP | MAX | UNITS |
|--|--|-----|-------|-----|-------|
| UNDERVOLTAGE LOCKOUT | | | | | |
| START Threshold | ISL78840A, ISL78841A | - | 7.0 | - | V |
| | ISL78843A, ISL78845A | - | 8.4 | - | V |
| STOP Threshold | ISL78840A, ISL78841A | - | 6.6 | - | V |
| | ISL78843A, ISL78845A | - | 7.6 | - | V |
| Hysteresis | ISL78840A, ISL78841A | - | 0.4 | - | V |
| | ISL78843A, ISL78845A | - | 0.8 | - | V |
| Start-up Current, I _{DD} | V _{DD} < START Threshold | - | 90 | - | μΑ |
| | V _{DD} < START Threshold, 100krad | - | 300 | - | μΑ |
| Operating Current, I _{DD} | (Note 3) | - | 2.9 | - | mA |
| Operating Supply Current, I _D | Includes 1nF GATE loading | - | 4.75 | - | mA |
| REFERENCE VOLTAGE | | | | | 1 |
| Overall Accuracy | Over line (V _{DD} = 9V to 13.2V), load 1mA and 10mA, temperature | - | 5.000 | - | V |
| Long Term Stability | $T_A = +125$ °C, 1000 hours (Note 4) | - | 5 | - | mV |
| Current Limit, Sourcing | | - | - | - | mA |
| Current Limit, Sinking | | - | - | - | mA |
| CURRENT SENSE | | | 1 | | 1 |
| Input Bias Current | V _{CS} = 1V | - | - | - | μΑ |
| Input Signal, Maximum | | - | 1.00 | - | V |
| Gain, $A_{CS} = \Delta V_{COMP}/\Delta V_{CS}$ | 0 < V _{CS} < 910mV, V _{FB} = 0V | - | 3.0 | | V/V |
| CS to OUT Delay | | - | 35 | - | ns |
| ERROR AMPLIFIER | | | | | 1 |
| Open Loop Voltage Gain | (Note 4) | - | 90 | - | dB |
| Unity Gain Bandwidth | (Note 4) | - | 1.5 | - | MHz |
| Reference Voltage | $V_{FB} = V_{COMP}$ | - | 2.500 | - | V |
| FB Input Bias Current | V _{FB} = 0V | - | -0.2 | - | μΑ |
| COMP Sink Current | $V_{COMP} = 1.5V, V_{FB} = 2.7V$ | - | - | - | mA |
| COMP Source Current | $V_{COMP} = 1.5V, V_{FB} = 2.3V$ | - | - | - | mA |
| COMP VOH | V _{FB} = 2.3V | - | - | - | V |
| COMP VOL | V _{FB} = 2.7V | - | - | - | V |
| PSRR | Frequency = 120Hz, V _{DD} = 9V to 13.2V (Note 4) | - | 80 | - | dB |
| OSCILLATOR | | | | | 1 |
| Frequency Accuracy | Initial, T _A = +25°C | - | 51 | - | kHz |
| Frequency Variation with V _{DD} | $T_A = +25$ °C, $(f_{13.2V} - f_{9V})/f_{12V}$ | - | 0.2 | - | % |
| Temperature Stability | (Note 4) | - | 5 | - | % |
| Amplitude, Peak-to-Peak | Static Test | - | 1.75 | - | V |
| RTCT Discharge Voltage (Valley Voltage) | Static Test | - | 1.0 | - | V |
| Discharge Current | RTCT = 2.0V | - | 7.8 | - | mA |
| OUTPUT | · | | 1 | | 1 |

Electrical Specifications

Recommended operating conditions unless otherwise noted. Refer to Block Diagram and Typical Application schematic on page 3 and page 4. $V_{DD}=13.2V,\ R_T=10k\Omega,\ C_T=3.3nF,\ T_A=-55\ to\ +125^{\circ}C.$ Typical values are at $T_A=+25^{\circ}C.$

| PARAMETER | TEST CONDITIONS | MIN | TYP | MAX | UNITS |
|--|--------------------------------------|-----|------|-----|-------|
| Gate VOH | V_{DD} to OUT, $I_{OUT} = -100$ mA | - | 1.0 | - | V |
| Gate VOL | OUT to GND, I _{OUT} = 100mA | - | 1.0 | - | V |
| Peak Output Current | C _{OUT} = 1nF (Note 4) | - | 1.0 | - | А |
| Rise Time | C _{OUT} = 1nF | - | 35 | - | ns |
| Fall Time | C _{OUT} = 1nF | - | 20 | - | ns |
| OUTPUT OFF state leakage | $V_{DD} = 5V$ | - | - | - | μA |
| PWM | | · | | | |
| Maximum Duty Cycle (ISL78840A, ISL78843A) | $COMP = V_{REF}$ | - | 96.0 | - | % |
| Maximum Duty Cycle (ISL78841A, ISL78845A) | $COMP = V_{REF}$ | - | 48.0 | - | % |
| Minimum Duty Cycle | COMP = GND | - | - | - | % |

NOTES:

- 3. This is the V_{DD} current consumed when the device is active but not switching. Does not include gate drive current.
- 4. Limits established by characterization and are not production tested.
- SEE tests performed with VREF bypass capacitor of 0.22μF and F_{SW} = 200kHz. SEB/L tests done on a standalone open loop configuration. SET tests done in a closed loop configuration. For SEL no hard latch requiring manual intervention were observed. For more information see SEE test Report xxxx.

Typical Performance Curves

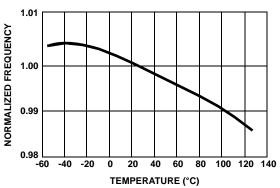


FIGURE 1. FREQUENCY vs TEMPERATURE

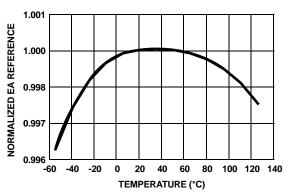


FIGURE 3. EA REFERENCE vs TEMPERATURE

Pin Descriptions

RTCT - This is the oscillator timing control pin. The operational frequency and maximum duty cycle are set by connecting a resistor, RT, between V_{REF} and this pin and a timing capacitor, CT, from this pin to GND. The oscillator produces a sawtooth waveform with a programmable frequency range up to 2.0MHz. The charge time, t_{C} , the discharge time, t_{D} , the switching frequency, f, and the maximum duty cycle, D_{MAX} , can be approximated from the Equations 1 through 4:

$$t_{\rm C} \approx 0.533 \cdot {\rm RT} \cdot {\rm CT}$$
 (EQ. 1)

$$t_{D} \approx -RT \cdot CT \cdot In \left(\frac{0.008 \cdot RT - 3.83}{0.008 \cdot RT - 1.71} \right)$$
 (EQ. 2)

$$f = 1/(t_C + t_D)$$
 (EQ. 3)

$$D = t_{C} \cdot f \tag{EQ. 4}$$

The formulae have increased error at higher frequencies due to propagation delays. Figure 4 may be used as a guideline in selecting the capacitor and resistor values required for a given switching frequency for the ISL78841, ISL78845ASRH. The value for the ISL78840, ISL78843ASRH will be twice that shown in Figure 4.

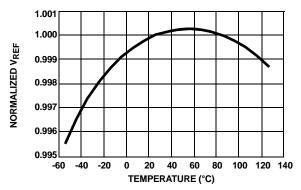


FIGURE 2. REFERENCE VOLTAGE vs TEMPERATURE

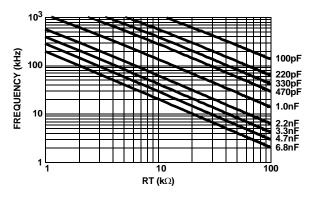


FIGURE 4. RESISTANCE FOR CT CAPACITOR VALUES GIVEN

COMP - COMP is the output of the error amplifier and the input of the PWM comparator. The control loop frequency compensation network is connected between the COMP and FB pins.

FB - The output voltage feedback is connected to the inverting input of the error amplifier through this pin. The non-inverting input of the error amplifier is internally tied to a reference voltage.

CS - This is the current sense input to the PWM comparator. The range of the input signal is nominally 0V to 1.0V and has an internal offset of 100mV.

 $\ensuremath{\mathbf{GND}}$ - $\ensuremath{\mathbf{GND}}$ is the power and small signal reference ground for all functions.

 ${\bf OUT}$ - This is the drive output to the power switching device. It is a high current output capable of driving the gate of a power MOSFET with peak currents of 1.0A. This GATE output is actively held low when ${\bf V}_{\rm DD}$ is below the UVLO threshold.

V_{DD} - V_{DD} is the power connection for the device. The total supply current will depend on the load applied to OUT. Total I_{DD} current is the sum of the operating current and the average output current. Knowing the operating frequency, f, and the MOSFET gate charge, Qq,

the average output current can be calculated from Equation 5:

$$I_{OLIT} = Qg \times f$$
 (EQ. 5)

To optimize noise immunity, bypass $\rm V_{DD}$ to GND with a ceramic capacitor as close to the $\rm V_{DD}$ and GND pins as possible.

 V_{REF} - The 5.00V reference voltage output. +1.0/-1.5% tolerance over line, load and operating temperature. The recommended bypass to GND cap is in the range 0.1μF to 0.22μF. A typical value of 0.15μF can be used.

Functional Description

Features

The ISL7884xASRH current mode PWM makes an ideal choice for low-cost flyback and forward topology applications. With its greatly improved performance over industry standard parts, it is the obvious choice for new designs or existing designs which require updating.

Oscillator

The ISL7884xASRH has a sawtooth oscillator with a programmable frequency range to 2MHz, which can be programmed with a resistor from V_{REF} and a capacitor to GND on the RTCT pin. (Please refer to Figure 4 for the resistor and capacitance required for a given frequency).

Soft-Start Operation

Soft-start must be implemented externally. One method, illustrated below, clamps the voltage on COMP.

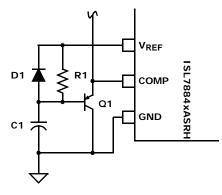


FIGURE 5. SOFT-START

The COMP pin is clamped to the voltage on capacitor C_1 plus a base-emitter junction by transistor Q_1 . C_1 is charged from V_{REF} through resistor R_1 and the base current of Q_1 . At power-up C_1 is fully discharged, COMP is at ~0.7V, and the duty cycle is zero. As C1 charges, the voltage on COMP increases, and the duty cycle increases in proportion to the voltage on C_1 . When COMP reaches the steady state operating point, the control loop takes over and soft start is complete. C_1 continues to charge up to V_{REF} and no longer affects COMP. During power down, diode D1 quickly discharges C1 so that the soft start circuit is properly initialized prior to the next power on sequence.

Gate Drive

The ISL7884xASRH is capable of sourcing and sinking 1A peak current. To limit the peak current through the IC, an optional external resistor may be placed between the totem-pole output of the IC (OUT pin) and the gate of the MOSFET. This small series resistor also damps any oscillations caused by the resonant tank of the parasitic inductances in the traces of the board and the FET's input capacitance. TID environment of >50krads requires the use of a bleeder resistor of 10k from OUT pin to GND.

Slope Compensation

For applications where the maximum duty cycle is less than 50%, slope compensation may be used to improve noise immunity, particularly at lighter loads. The amount of slope compensation required for noise immunity is determined empirically, but is generally about 10% of the full scale current feedback signal. For applications where the duty cycle is greater than 50%, slope compensation is required to prevent instability.

Slope compensation may be accomplished by summing an external ramp with the current feedback signal or by subtracting the external ramp from the voltage feedback error signal. Adding the external ramp to the current feedback signal is the more popular method.

From the small signal current-mode model [1] it can be shown that the naturally-sampled modulator gain, Fm, without slope compensation is calculated in Equation 6:

$$Fm = \frac{1}{SnTsw}$$
 (EQ. 6)

where Sn is the slope of the sawtooth signal and tsw is the duration of the half-cycle. When an external ramp is added, the modulator gain becomes Equation 7:

$$Fm = \frac{1}{(Sn + Se)tsw} = \frac{1}{m_c Sntsw}$$
 (EQ. 7)

where Se is slope of the external ramp and becomes Equation 8:

$$m_c = 1 + \frac{Se}{Sn}$$
 (EQ. 8)

The criteria for determining the correct amount of external ramp can be determined by appropriately setting the damping factor of the double-pole located at the switching frequency. The double-pole will be critically damped if the Q-factor is set to 1, over-damped for Q < 1, and under-damped for Q > 1. An under-damped condition may result in current loop instability.

$$Q = \frac{1}{\pi(m_c(1-D)-0.5)}$$
 (EQ. 9)

where D is the percent of on time during a switching cycle. Setting Q=1 and solving for Se yields Equation 10:

$$S_e = S_n \left(\left(\frac{1}{\pi} + 0.5 \right) \frac{1}{1 - D} - 1 \right)$$
 (EQ. 10)

Since Sn and Se are the on time slopes of the current ramp and the external ramp, respectively, they can be multiplied by t_{ON} to obtain the voltage change that occurs during t_{ON} .

$$V_e = V_n \left(\left(\frac{1}{\pi} + 0.5 \right) \frac{1}{1 - D} - 1 \right)$$
 (EQ. 11)

where V_n is the change in the current feedback signal (ΔI) during the on time and Ve is the voltage that must be added by the external ramp.

For a flyback converter, Vn can be solved for in terms of input voltage, current transducer components, and primary inductance, yielding Equation 12:

$$V_{e} = \frac{D \cdot T_{SW} \cdot V_{IN} \cdot R_{CS}}{L_{p}} \left(\left(\frac{1}{\pi} + 0.5 \right) \frac{1}{1 - D} - 1 \right) \qquad V \tag{EQ. 12}$$

where R_{CS} is the current sense resistor, f_{SW} is the switching frequency, L_p is the primary inductance, $V_{\mbox{\footnotesize{IN}}}$ is the minimum input voltage, and D is the maximum duty cycle.

The current sense signal at the end of the ON time for CCM operation is Equation 13:

$$V_{CS} = \frac{N_S \cdot R_{CS}}{N_P} \left(I_O + \frac{(1 - D) \cdot V_O \cdot f_{SW}}{2L_S} \right) \qquad V$$
 (EQ. 13)

where V_{CS} is the voltage across the current sense resistor, L_{s} is the secondary winding inductance, and I_{O} is the output current at current limit. Equation 13 assumes the voltage drop across the output rectifier is negligible.

Since the peak current limit threshold is 1.00V, the total current feedback signal plus the external ramp voltage must sum to this value when the output load is at the current limit threshold as shown in Equation 14.

$$V_e + V_{CS} = 1$$
 (EQ. 14)

Substituting Equations 12 and 13 into Equation 14 and solving for R_{CS} yields Equation 15:

$$R_{CS} = \frac{1}{\frac{D \cdot f_{sw} \cdot V_{IN}}{L_{p}} \cdot \left(\frac{\frac{1}{\pi} + 0.5}{1 - D} - 1\right) + \frac{N_{s}}{N_{p}} \cdot \left(I_{O} + \frac{(1 - D) \cdot V_{O} \cdot f_{sw}}{2L_{s}}\right)}$$

(EQ. 15)

Adding slope compensation is accomplished in the ISL7884xASRH using an external buffer transistor and the RTCT signal. A typical application sums the buffered

RTCT signal with the current sense feedback and applies the result to the CS pin as shown in Figure 6.

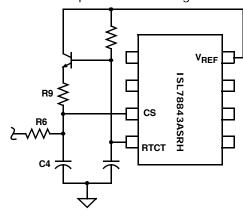


FIGURE 6. SLOPE COMPENSATION

Assuming the designer has selected values for the RC filter (R_6 and C_4) placed on the CS pin, the value of R_9 required to add the appropriate external ramp can be found by superposition.

$$V_{e} = \frac{2.05D \cdot R_{6}}{R_{6} + R_{9}} \qquad V \tag{EQ. 16}$$

The factor of 2.05 in Equation 16 arises from the peak amplitude of the sawtooth waveform on RTCT minus a base-emitter junction drop. That voltage multiplied by the maximum duty cycle is the voltage source for the slope compensation. Rearranging to solve for R₉ yields Equation 17:

$$R_9 = \frac{(2.05D - V_e) \cdot R_6}{V_e} \qquad \Omega$$
 (EQ. 17)

The value of R_{CS} determined in Equation 15 must be rescaled so that the current sense signal presented at the CS pin is that predicted by Equation 13. The divider created by R_6 and R_9 makes this necessary.

$$R'_{CS} = \frac{R_6 + R_9}{R_9} \cdot R_{CS}$$
 (EQ. 18)

Example:

$$V_{IN} = 12V$$

$$V_0 = 48V$$

$$L_{s} = 800 \mu H$$

$$Ns/Np = 10$$

$$Lp = 8.0\mu H$$

$$I_0 = 200 \text{mA}$$

Switching Frequency, $f_{SW} = 200kHz$

Duty Cycle,
$$D = 28.6\%$$

$$R_6 = 499\Omega$$

Solve for the current sense resistor, R_{CS} , using Equation 15.

FN6991.1 August 19, 2010

 $R_{CS} = 295 m\Omega$

Determine the amount of voltage, Ve, that must be added to the current feedback signal using Equation 12.

Ve = 92.4mV

Using Equation 17, solve for the summing resistor, R_9 , from CT to CS.

 $R_9 = 2.67k\Omega$

Determine the new value of R_{CS} (R'_{CS}) using Equation 18.

 $R'_{CS} = 350 m\Omega$

Additional slope compensation may be considered for design margin. The above discussion determines the minimum external ramp that is required. The buffer transistor used to create the external ramp from RTCT should have a sufficiently high gain (>200) so as to minimize the required base current. Whatever base current is required reduces the charging current into RTCT and will reduce the oscillator frequency.

Fault Conditions

A Fault condition occurs if V_{REF} falls below 4.65V. When a Fault is detected OUT is disabled. When V_{REF} exceeds 4.80V, the Fault condition clears, and OUT is enabled.

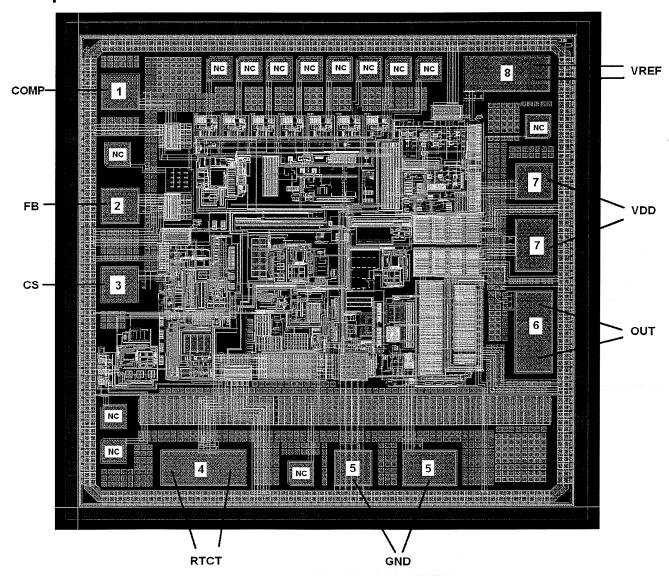
Ground Plane Requirements

Careful layout is essential for satisfactory operation of the device. A good ground plane must be employed. A unique section of the ground plane must be designated for high di/dt currents associated with the output stage. $V_{\mbox{DD}}$ should be bypassed directly to GND with good high frequency capacitors.

References

[1] Ridley, R., "A New Continuous-Time Model for Current Mode Control", IEEE Transactions on Power Electronics, Vol. 6, No. 2, April 1991.

Die Map



Revision History

The revision history provided is for informational purposes only and is believed to be accurate, but not warranted. Please go to web to make sure you have the latest Rev.

| DATE | REVISION | CHANGE |
|----------|----------|--|
| 4/22/10 | FN6991.1 | Added Electrical Spec Table showing only the typical values. Removed boldface over-temp limit notes. |
| 4/8/10 | | Added SBDIP parts, pinout and Flatpack & SBDIP PODs. |
| 12/21/09 | FN6991.0 | Initial pre-release |

Products

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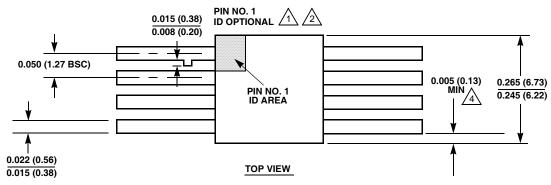
*For a complete listing of Applications, Related Documentation and Related Parts, please see the respective device information page on intersil.com: ISL78840ASRH, ISL78845ASRH, <a href="IS

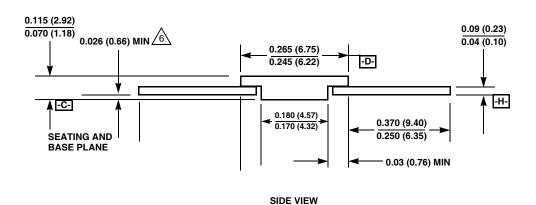
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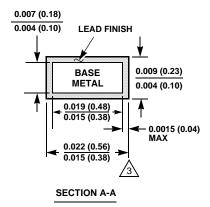
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Package Outline Drawing

K8.A 8 LEAD CERAMIC METAL SEAL FLATPACK PACKAGE Rev 1, 1/10







NOTES:

1. Index area: A notch or a pin one identification mark shall be located adjacent to pin one and shall be located within the shaded area shown. The manufacturer's identification shall not be used as a pin one identification mark. Alternately, a tab may be used to identify pin one.

1 f a pin one identification mark is used in addition to a tab, the limits of the tab dimension do not apply.

The maximum limits of lead dimensions (section A-A) shall be measured at the centroid of the finished lead surfaces, when solder dip or tin plate lead finish is applied.

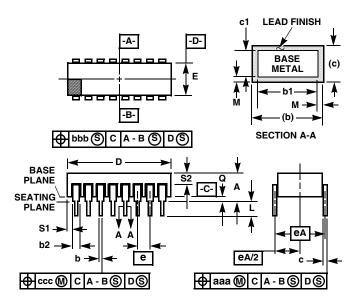
4 Measure dimension at all four corners.

5. For bottom-brazed lead packages, no organic or polymeric materials shall be molded to the bottom of the package to cover the leads.

6\ Dimension shall be measured at the point of exit (beyond the meniscus) of the lead from the body. Dimension minimum shall be reduced by 0.0015 inch (0.038mm) maximum when solder dip lead finish is applied.

- 7. Dimensioning and tolerancing per ANSI Y14.5M 1982.
- 8. Controlling dimension: INCH.

Ceramic Dual-In-Line Metal Seal Packages (SBDIP)



NOTES:

- 1. Index area: A notch or a pin one identification mark shall be located adjacent to pin one and shall be located within the shaded area shown. The manufacturer's identification shall not be used as a pin one identification mark.
- 2. The maximum limits of lead dimensions b and c or M shall be measured at the centroid of the finished lead surfaces, when solder dip or tin plate lead finish is applied.
- 3. Dimensions b1 and c1 apply to lead base metal only. Dimension M applies to lead plating and finish thickness.
- 4. Corner leads (1, N, N/2, and N/2+1) may be configured with a partial lead paddle. For this configuration dimension b3 replaces dimension b2.
- 5. Dimension Q shall be measured from the seating plane to the base plane.
- 6. Measure dimension S1 at all four corners.
- 7. Measure dimension S2 from the top of the ceramic body to the nearest metallization or lead.
- 8. N is the maximum number of terminal positions.
- 9. Braze fillets shall be concave.
- 10. Dimensioning and tolerancing per ANSI Y14.5M 1982.
- 11. Controlling dimension: INCH.

D8.3 MIL-STD-1835 CDIP2-T8 (D-4, CONFIGURATION C) 8 LEAD CERAMIC DUAL-IN-LINE METAL SEAL PACKAGE

| | INCHES | | MILLIMETERS | | |
|--------|-----------|------------------|-------------|------------------|-------|
| SYMBOL | MIN | MAX | MIN | MAX | NOTES |
| Α | - | 0.200 | - | 5.08 | - |
| b | 0.014 | 0.026 | 0.36 | 0.66 | 2 |
| b1 | 0.014 | 0.023 | 0.36 | 0.58 | 3 |
| b2 | 0.045 | 0.065 | 1.14 | 1.65 | - |
| b3 | 0.023 | 0.045 | 0.58 | 1.14 | 4 |
| С | 0.008 | 0.018 | 0.20 | 0.46 | 2 |
| c1 | 0.008 | 0.015 | 0.20 | 0.38 | 3 |
| D | - | 0.405 | - | 10.29 | - |
| Е | 0.220 | 0.310 | 5.59 | 7.87 | - |
| е | 0.100 BSC | | 2.54 BSC | | - |
| eA | 0.300 BSC | | 7.62 BSC | | - |
| eA/2 | 0.150 | 0.150 BSC | | BSC | - |
| L | 0.125 | 0.200 | 3.18 5.08 | | - |
| Q | 0.015 | 0.060 | 0.38 | 1.52 | 5 |
| S1 | 0.005 | - | 0.13 | - | 6 |
| S2 | 0.005 | - | 0.13 | - | 7 |
| α | 90° | 105 ⁰ | 90° | 105 ⁰ | - |
| aaa | - | 0.015 | - | 0.38 | - |
| bbb | - | 0.030 | - | 0.76 | - |
| ccc | - | 0.010 | - | 0.25 | - |
| М | - | 0.0015 | - | 0.038 | 2 |
| N | 8 | | 8 | | 8 |

Rev. 0 4/94

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